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ABSTRACT OF THE DISCLOSURE

MEMBER FOR PRODUCTION DEVICE OF SEMICONDUCTOR

A member for production device of a group III-V compound semiconductor which is superior in chemical and mechanical stabilities is provided, thereby providing a high-productivity production device which is suitable for the compound semiconductor.

(1) In the member for production device of a group III-V compound semiconductor represented by the general formula $In_xGa_yAl_zN$ (provided that $x + y + z = 1$, $0 \leqq x \leqq 1$, $0 \leqq y \leqq 1$, and $0 \leqq z \leqq 1$), the improvement comprising SiC which is obtained by converting a graphite base material is converted into SiC.

(2) In the member for production device of a group III-V compound semiconductor represented by the general formula $In_xGa_yAl_zN$ (provided that $x + y + z = 1$, $0 \leqq x \leqq 1$, $0 \leqq y \leqq 1$, and $0 \leqq z \leqq 1$), the improvement comprising using a graphite-SiC composite wherein at least surface layer part of a graphite substrate is converted into SiC.

(3) A production device of a group III-V compound semiconductor which is characterized by using the member for production device of the group III-V compound semiconductor of (1) or (2).